

1-Line Low Capacitance Bi-directional TVS Diode

Description

The DESD3Z3V3ULA is a 5V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast re-sponse time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The DESD3Z3V3ULA has a low capacitance with a typical value at 1pF, and complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a lead-free SOD-323 package. The small size, low capacitance and high ESD surge protection make DESD3Z3V3ULA an ideal choice to protect cell phone, wireless systems, and communication equipment.

Features

- 360W peak pulse power (8/20 μs)
- Ultra low capacitance: 1pF typical
- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Low clamping voltage
- Protects one power line or data line
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: $\pm 30\text{kV}$
Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 21A (8/20 μs)
- RoHS Compliant

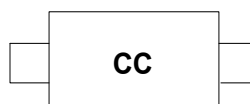
Mechanical Characteristics

- Package: SOD-323
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

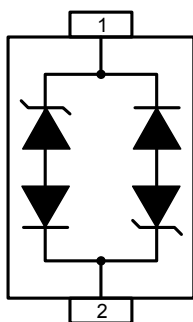
Applications

- USB Ports
- Smart Phones
- Wireless Systems
- Ethernet 10/100/1000 Base T

Marking Information



Dimensions and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
DESD3Z3V3ULA	3000	7 inch

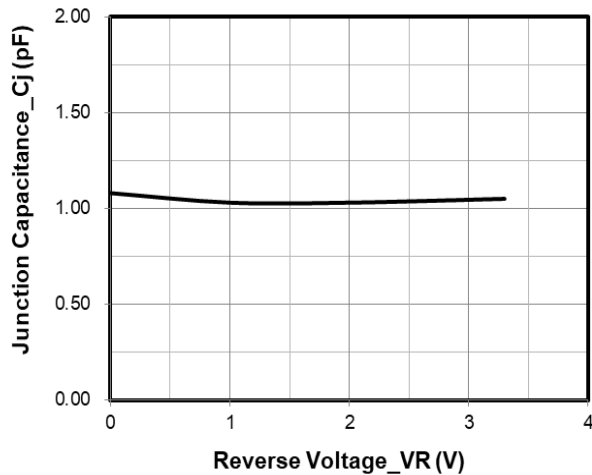
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	350	W
Peak Pulse Current (8/20 μs)	I _{PP}	21	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	± 30 ± 30	kV
Operating Temperature Range	T _J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^{\circ}\text{C}$

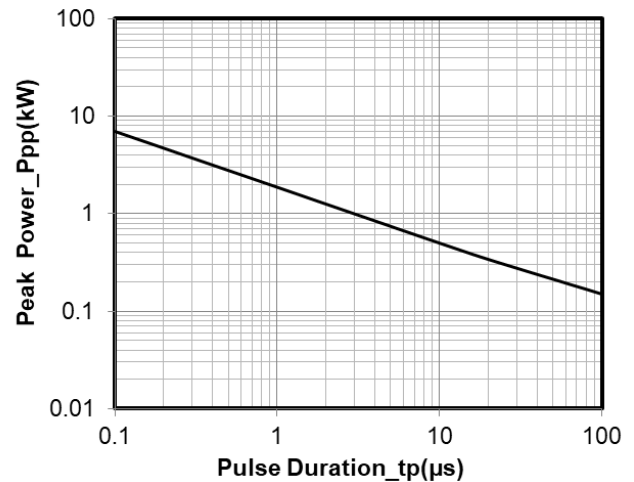
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			3.3	V	
Punch-Through Voltage	V _{PT}	3.5			V	I _T = 2 μA
Snap-Back Voltage	V _{BR}	2.8			V	I _T = 50mA
Reverse Leakage Current	I _R			0.5	μA	V _{RWM} = 3.3V
Clamping Voltage	V _C			5	V	I _{PP} = 1A (8 x 20 μs pulse)
Clamping Voltage	V _C			16	V	I _{PP} = 21A (8 x 20 μs pulse)
Junction Capacitance	C _J		0.8	1.5	pF	V _R = 0V, f = 1MHz

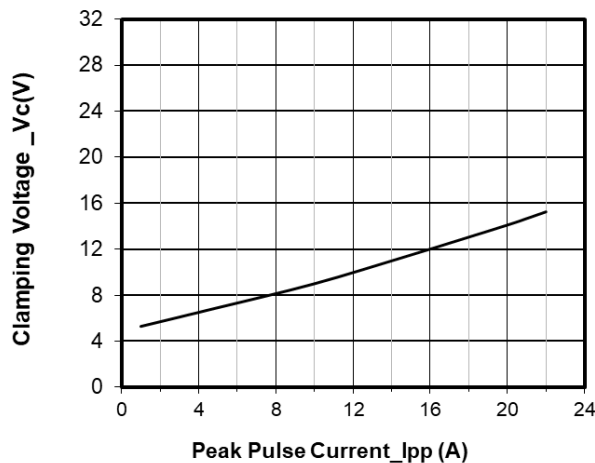
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



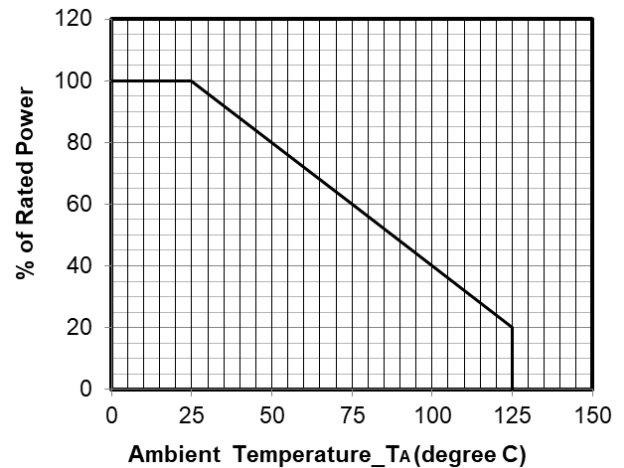
Junction Capacitance vs. Reverse Voltage



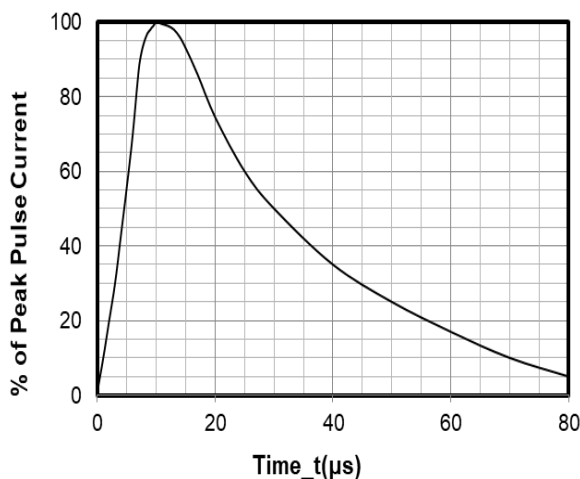
Peak Pulse Power vs. Pulse Time



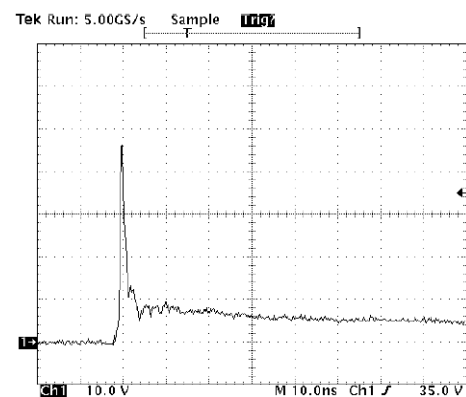
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform



Note: Data is taken with a 10x attenuator

ESD Clamping Voltage

8 kV Contact per IEC61000-4-2